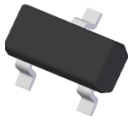
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3KV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

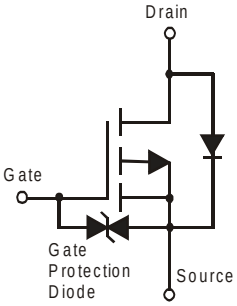
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

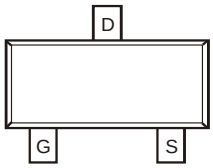
SOT23



Top View



Internal Schematic



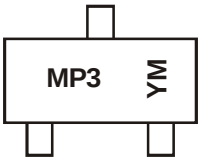
Top View

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2035U-7	Standard	SOT23	3,000 / 7" Tape & Reel
DMP2035UQ-7	Automotive	SOT23	3,000 / 7" Tape & Reel
DMP2035U-13	Standard	SOT23	10,000 / 13" Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MP3 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: D = 2016)
M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2016	2017	2018	2019	2020	2021	2022
Code	W	~	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +70°C	I_D	-3.6 -2.9	A
Pulsed Drain Current (Note 6)			I_{DM}	-24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.81	W
Thermal Resistance, Junction to Ambient @T_A = +25°C	$R_{\theta JA}$	153.5	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.7	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	23	35	mΩ	V_{GS} = -4.5V, I_D = -4.0A
			30	45		V_{GS} = -2.5V, I_D = -4.0A
			41	62		V_{GS} = -1.8V, I_D = -2.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	14	—	S	V_{DS} = -5V, I_D = -4A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1,610	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	157	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	145	—	pF	
Gate Resistance	R_g	—	9.45	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	15.4	—	nC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -4A
Gate-Source Charge	Q_{gs}	—	2.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.3	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	16.8	—	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_L = 10Ω, R_G = 6.0Ω, I_D = -1A
Turn-On Rise Time	t_r	—	12.4	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	94.1	—	ns	
Turn-Off Fall Time	t_f	—	42.4	—	ns	

Notes: 5. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width t ≦10s.
6. Repetitive rating, pulse width limited by junction temperature.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

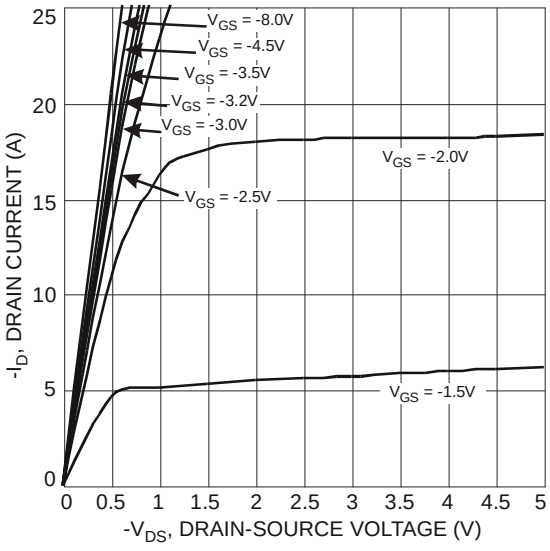


Fig. 1 Typical Output Characteristic

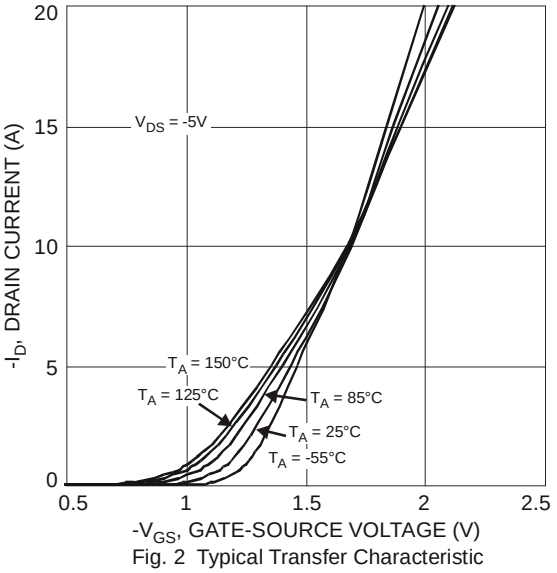


Fig. 2 Typical Transfer Characteristic

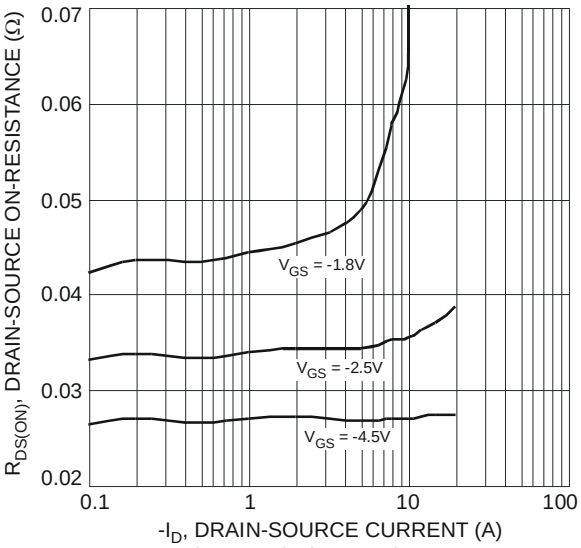


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

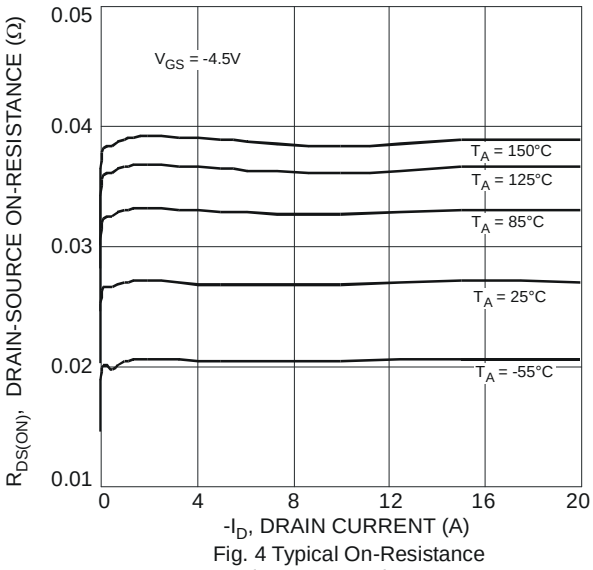


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

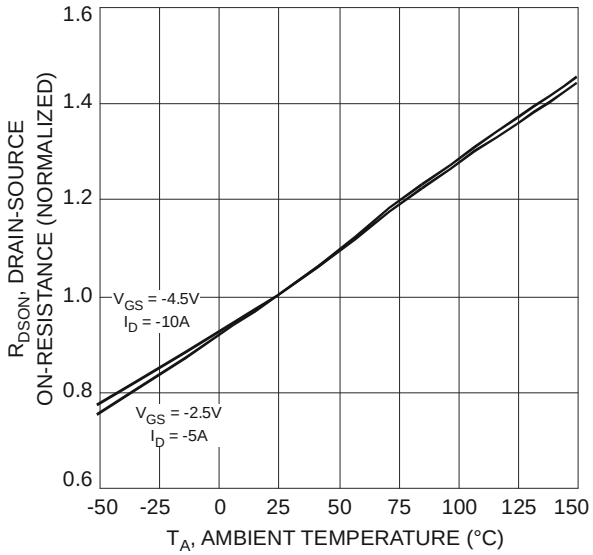


Fig. 5 On-Resistance Variation with Temperature

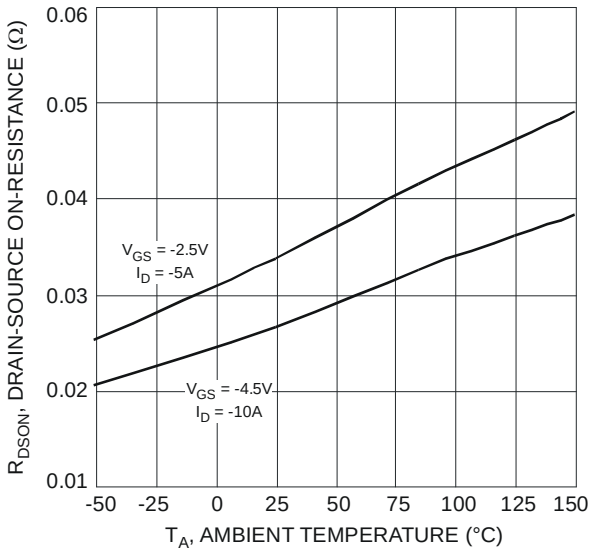


Fig. 6 On-Resistance Variation with Temperature

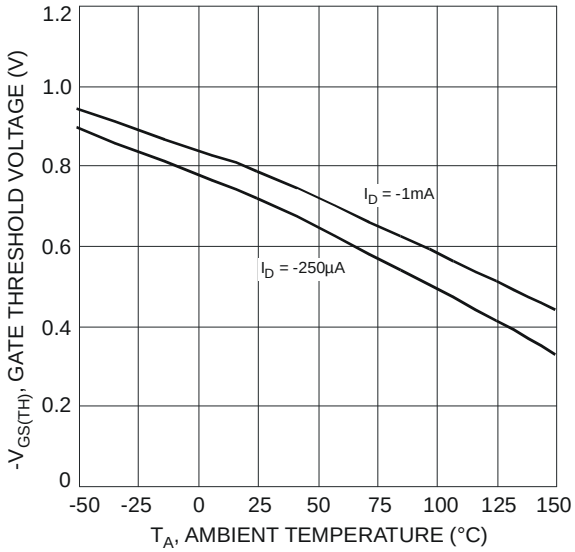


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

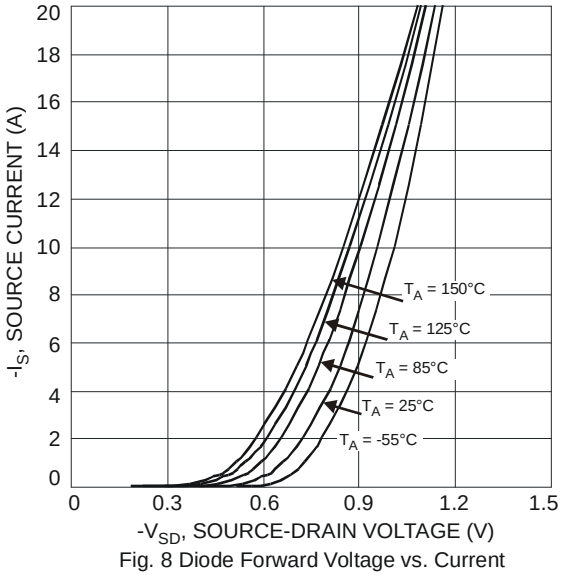


Fig. 8 Diode Forward Voltage vs. Current

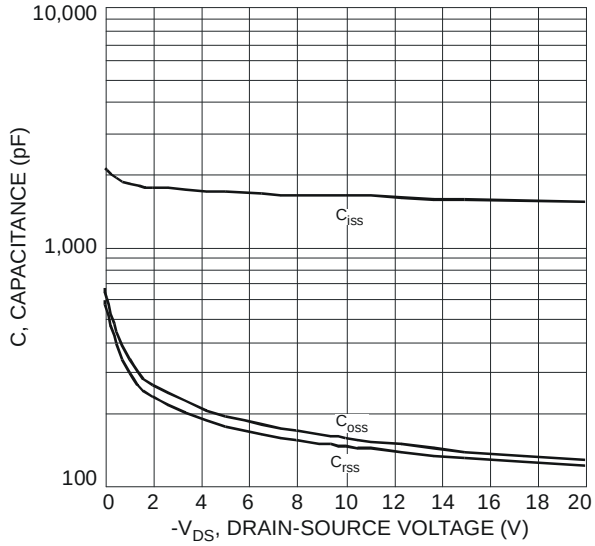


Fig. 9 Typical Total Capacitance

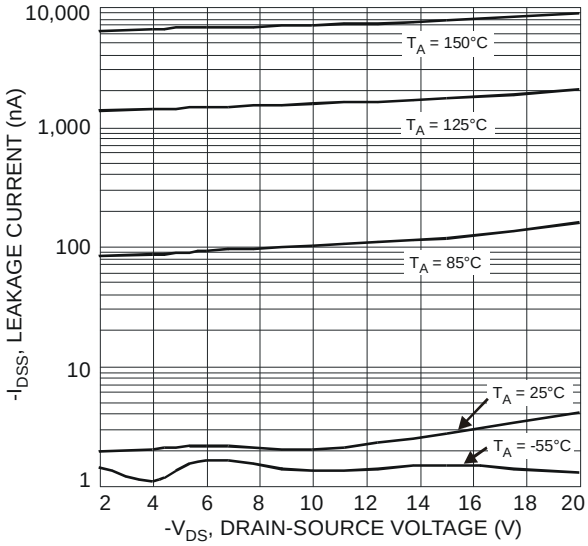


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

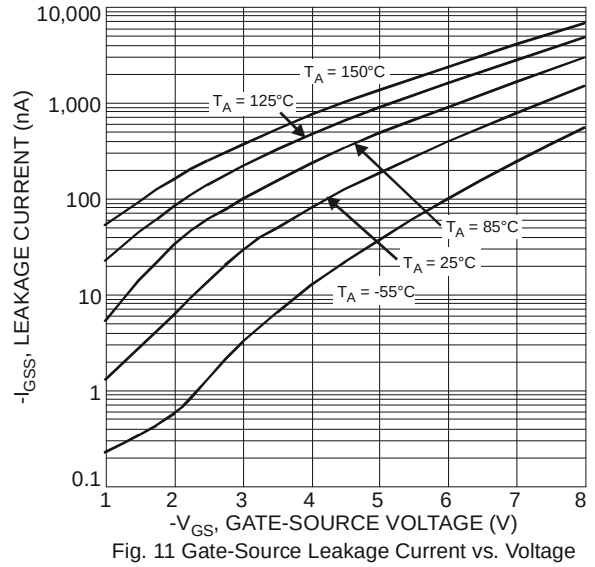


Fig. 11 Gate-Source Leakage Current vs. Voltage

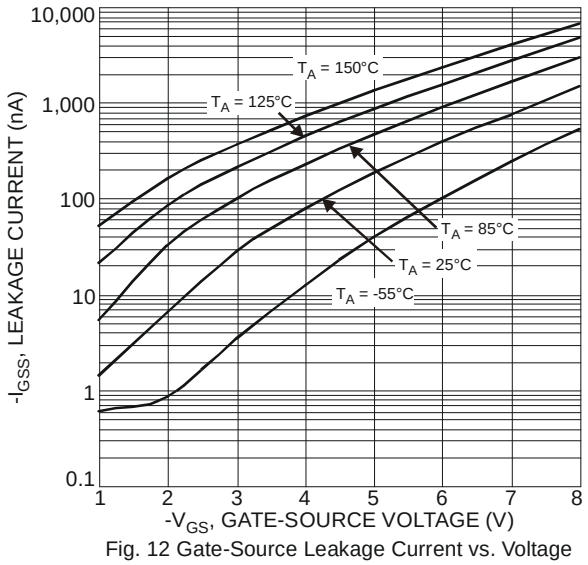


Fig. 12 Gate-Source Leakage Current vs. Voltage

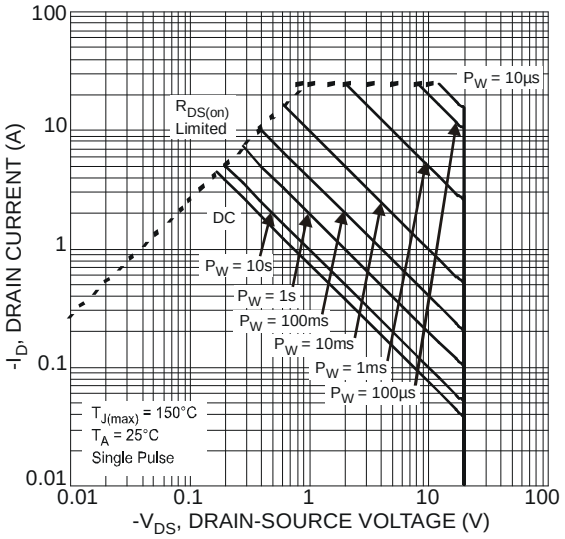


Fig. 13 SOA, Safe Operation Area

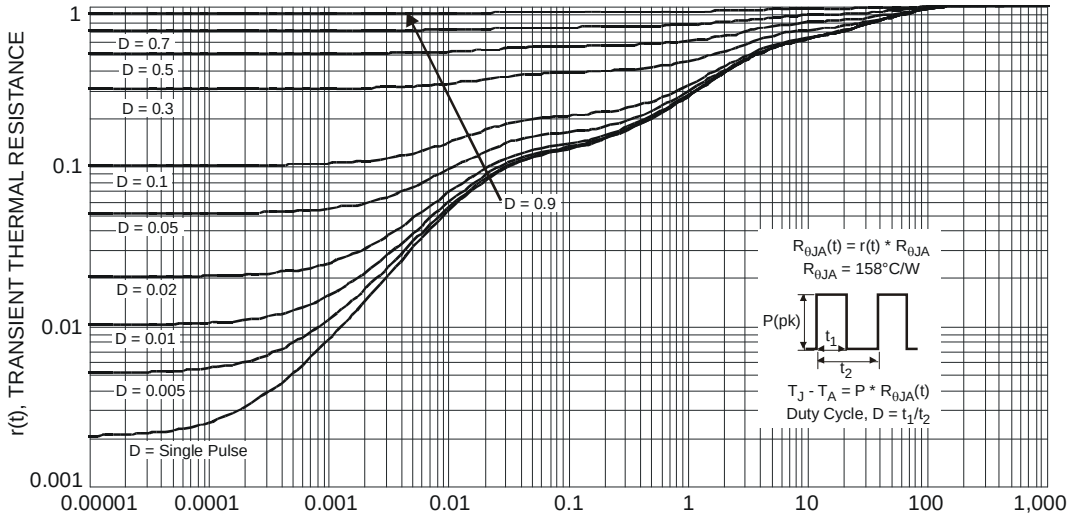
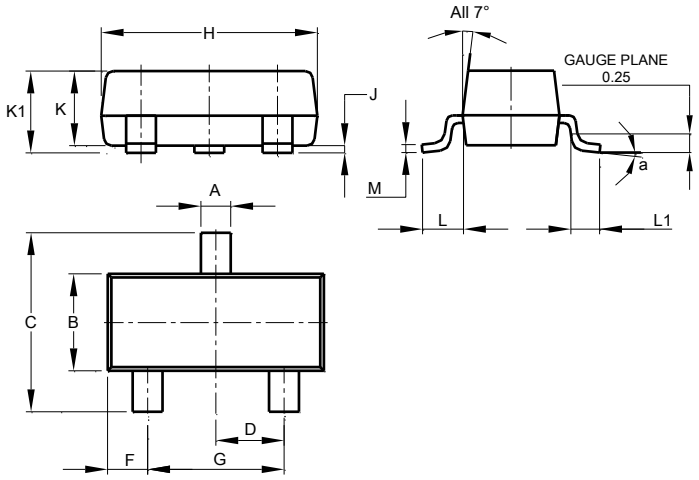


Fig. 14 Transient Thermal Response

Package Outline Dimensions

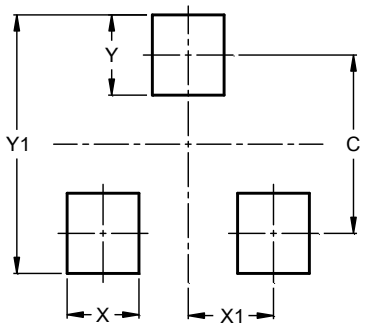
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9